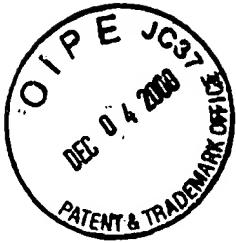


6 AM 2813



IN THE UNITED STATES PATENT AND TRADEMARK OFFICE

Applicant: Gurtej Singh Sandhu et al.

Title: METHOD TO REDUCE FIXED CHARGE IN CVD OZONE DEPOSITED FILMS

Docket No.: 303.573US1

Serial No.: 08/636,069

Filed: April 22, 1996

Due Date: November 30, 2000

Examiner: Erik Kielin

Group Art Unit: 2813

Commissioner for Patents
Washington, D.C. 20231

We are transmitting herewith the following attached items (as indicated with an "X"):

A return postcard.
 An Amendment and Response (10 Pages).

Please consider this a PETITION FOR EXTENSION OF TIME for sufficient number of months to enter these papers and please charge any additional required fees or credit overpayment to Deposit Account No. 19-0743.

SCHWEGMAN, LUNDBERG, WOESSNER & KLUTH, P.A.
P.O. Box 2938, Minneapolis, MN 55402 (612-373-6900)

By 
Atty: Leoniede M. Brennan
Reg. No. 35,832

CERTIFICATE UNDER 37 CFR 1.8: The undersigned hereby certifies that this correspondence is being deposited with the United States Postal Service with sufficient postage as first class mail, in an envelope addressed to: Commissioner for Patents, Washington, D.C. 20231, on this 30 day of November, 2000.

Name

Amy Moravian

Signature

Amy Moravian

Customer Number 21186

SCHWEGMAN, LUNDBERG, WOESSNER & KLUTH, P.A.

P.O. Box 2938, Minneapolis, MN 55402 (612-373-6900)

(GENERAL)

S/N 08/636,069

PATENT

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AMENDMENT AND RESPONSE UNDER 37 CFR § 1.111

Commissioner for Patents
Washington, D.C. 20231

Applicant has reviewed the Office Action mailed on August 30, 2000. Please amend the above-identified patent application as follows.

IN THE CLAIMS

Please cancel claim 37 without prejudice or disclaimer thereto.

Please amend the claims as follows:

1.(Amended) A chemical vapor deposition (CVD) process for depositing borophosphosilicate glass films on a substrate surface, the process comprising:
disposing the substrate within a chemical vapor deposition reaction chamber;
heating the substrate to a temperature within a range of at least 480°C to about 700°C;
introducing a gas volume of SiO₂ precursors into the chamber;
admitting a gas volume of ozone into the chamber;
admitting a dopant source for phosphorus into the chamber;
admitting a dopant source for boron into the chamber; and
exposing a reaction volume of gases above the substrate surface to a high intensity light source to increase the functional atomic oxygen concentration and reduce the fixed charge in the deposited films; and
subjecting the reaction volume of gas to a pressure of approximately 200 to 760 torr during deposition of the borophosphosilicate layer.

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